TECHNICAL DATA DATA SHEET 553, REV. A

HERMETIC POWER MOSFET N-CHANNEL

FEATURES:

- 500 Volt, 0.85, Ohm, 5.5Amp MOSFET
- Isolated and Hermetically Sealed
- Surface Mount Package

MAXIMUM RATINGS

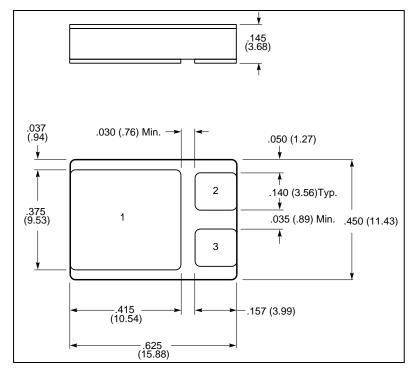
ALL RATINGS ARE AT $T_A = 25$ °C UNLESS OTHERWISE SPECIFIED.

RATING	SYMBOL	MIN.	TYP.	MAX.	UNITS
GATE TO SOURCE VOLTAGE	V_{GS}	-	-	±20	Volts
CONTINUOUS DRAIN CURRENT $T_C = 25$ °C	I _D	-	-	5.5	Amps
PULSED DRAIN CURRENT @ T _C = 25°C	I _{DM}	-	-	22	Amps
OPERATING AND STORAGE TEMPERATURE	T_{OP}/T_{STG}	-55	-	+150	°C
TERMAL RESISTANCE JUNCTION TO CASE	$R_{\theta JC}$	-	-	0.62	°C/W
TOTAL DEVICE DISSIPATION @ T _C = 25°C	P_{D}	-	-	200	Watts

ELECTRICAL CHARACTERISTICS

DRAIN TO SOURCE BREAKDOWN VOLTAGE	BV _{DSS}	500	-	-	Volts
$V_{GS} = 0V$, $I_D = 1.0$ mA					
DRAIN TO SOURCE ON STATE RESISTANCE		-	-		Ω
$V_{GS} = 10V, I_{D} = 3.5A$	R _{DS(ON)}			0.85	
GATE THRESHOLD VOLTAGE $V_{DS} = V_{GS}$, $I_D = 250 \mu A$	$V_{GS(th)}$	2.0	-	4.0	Volts
FORWARD TRANSCONDUCTANCE	g_{fs}	4.7	-	-	S(1/Ω)
$V_{DS} \ge 15V$, $I_{D} = 3.5A$					
ZERO GATE VOLTAGE DRAIN CURRENT, $T_J = 25^{\circ}C$	I_{DSS}	-	-	25	
$(V_{DS} = 0.8 \text{ x Max. Rating}, V_{GS} = 0V), T_{J} = 125^{\circ}C$				250	μΑ
GATE TO SOURCE LEAKAGE FORWARD V _{GS} = 20V	I _{GSS}	-	-	100	nA
GATE TO SOURCE LEAKAGE REVERSE $V_{GS} = -20V$				-100	
TOTAL GATE CHARGE $V_{GS} = 10V$,	Q_g	-	-	68.5	
GATE TO SOURCE CHARGE $V_{DS} = 250V$,	Q_{gs}			12.5	nC
GATE TO DRAIN CHARGE $I_D = 5.5A$	Q_gd			40.5	
TURN ON DELAY TIME $V_{DD} = 250V$,	$t_{d(ON)}$	-	21	-	
RISE TIME $I_D = 5.5A$,	t _r		73		nsec
TURN OFF DELAY TIME $R_G = 9.1\Omega$,	$t_{d(OFF)}$		72		
FALL TIME $V_{GS} = 10V$	t _f		51		
CONTIUOUS SOURCE CURRENT	I _S	-	5.5	-	Amps
DIODE FORWARD VOLTAGE $T_J = 25^{\circ}\text{C}, I_S = 5.5\text{V}$	V_{SD}	-	-	1.5	Volts
$V_{GS} = 0V$					
REVERSE RECOVERY TIME $T_J = 25$ °C,	t _{rr}	-	-	700	nsec
$I_{S} = 5.5A,$					
$di/dt \le = -100A/\mu sec$	_				
REVERSE RECOVERY CHARGE $V_{DD} \le 50V$	Q_{rr}			8.9	μС
INPUT CAPACITANCE $V_{GS} = 0V, V_{DS} = 25V,$	C_{iss}	-	1300	-	
OUTPUT CAPACITANCE f = 1.0MHz	C_{oss}		310		pF
REVERSE TRANSFER CAPACITANCE	C_{rss}		120		

MECHANICAL DIMENSIONS: in Inches / mm



SMD-1

PINOUT TABLE

DEVICE TYPE	PIN 1	PIN 2	PIN 3
MOSFET	DRAIN	SOURCE	GATE
LCC-3P PACKAGE			

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